

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**Priority** Application Serial No. .... 09/059,057  
**Priority** Filing Date .... April 10, 1998  
 Inventor ..... Vishnu K. Agarwal et al.  
 Assignee ..... Micron Technology, Inc.  
**Priority** Group Art Unit ..... 2822  
**Priority** Examiner ..... M. Guerrero  
 Attorney's Docket No. .... MI22-1299  
 Title: Capacitors and Methods of Forming Capacitors

3c542 U.S. PTO  
 09/428125  
 10/26/99

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449


In compliance with 37 C.F.R. §1.56, 1.97 and 1.98, your attention  
 is directed to the United States patents and other references listed on  
 the attached Form PTO-1449. No admission is made regarding whether  
 all the submitted references are prior art.

The listed references were cited by, or submitted to , the Office  
 in the parent, co-pending application of the above-identified application.  
 The above-identified application is a divisional application of co-pending  
 application Serial No. 09/059,057, filed April 10, 1998. Such prior  
 disclosure is sufficient for the above-identified application as far as  
 copies of the references are concerned. 37 C.F.R. §1.98(d) and MPEP  
 §609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: 10-26-99

By:   
 Mark S. Matkin  
 Reg. No. 32,268

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1299	SERIAL NO. 09/059,057
<b>LIST OF ART CITED BY APPLICANT</b> (Use several sheets if necessary)				APPLICANT VISHNU K. AGARWAL ET AL.	
				FILING DATE APRIL 10, 1998	GROUP 2822

JCE42 U.S. PTO  
09/28/98

U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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			Vol. 82, No. 9, pp. 4577-4585 (11/1997).					
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	AK	5,348,894	09/1994	GNADÉ ET AL.		
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	AR	KAMIYAMA, S. et al., <i>Ultrathin Tantalum Oxide Capacitor Dielectric Layers Fabricated Using Rapid Thermal Nitradation</i>				
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	AG	5,191,510	03/1993	HUFFMAN	
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